



1

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IDM

IDM

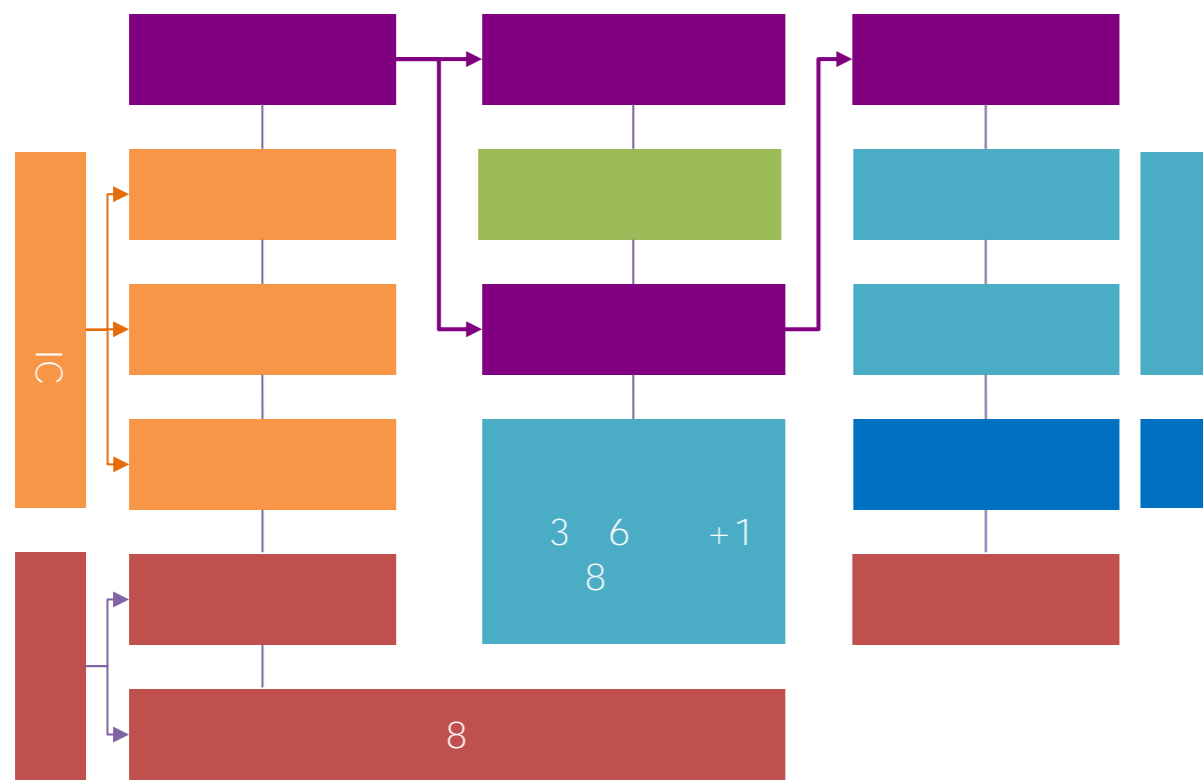
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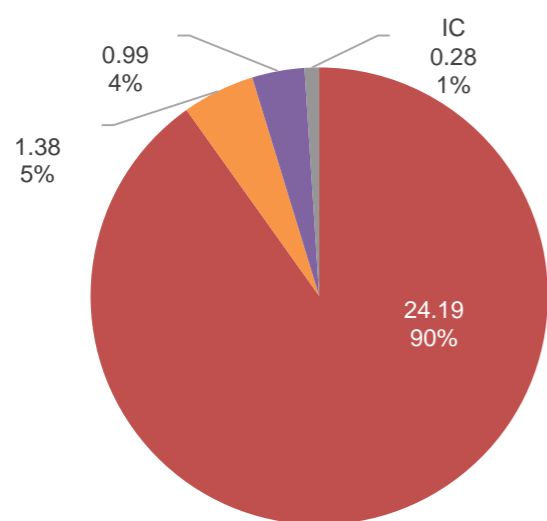
			2018
	3 6	Analog BCD MEMS DMOS Power Discrete	247
	1 8	Advance BCD Analog DMOS	



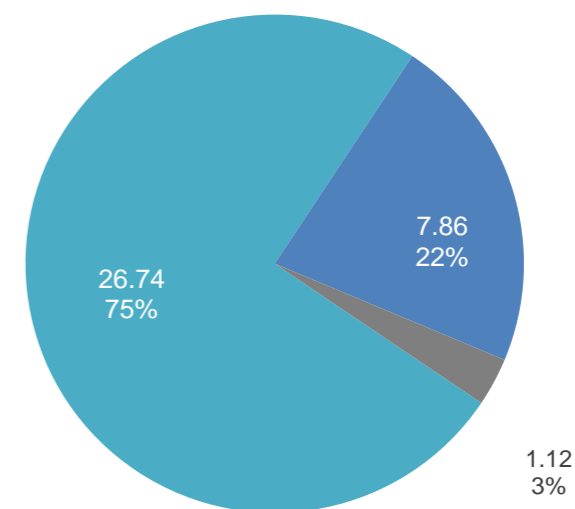
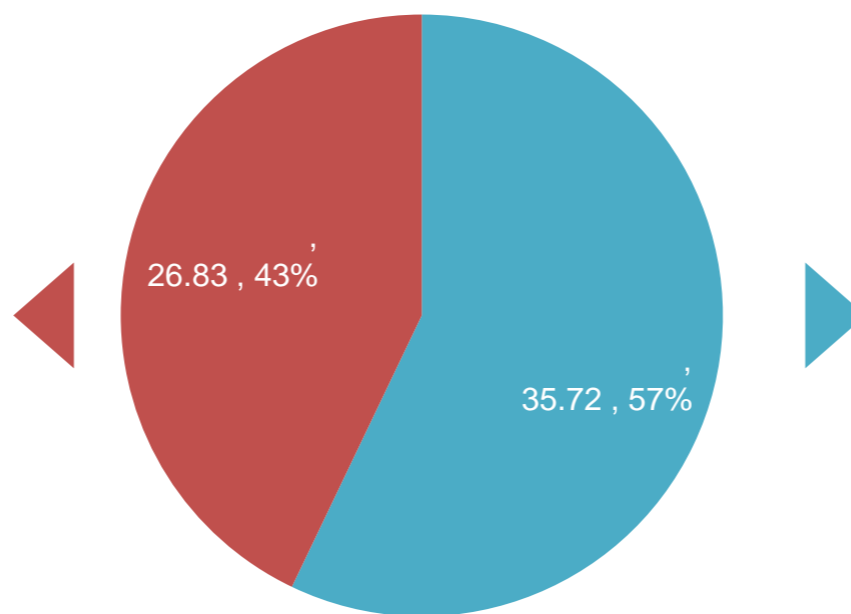
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TCL MPS

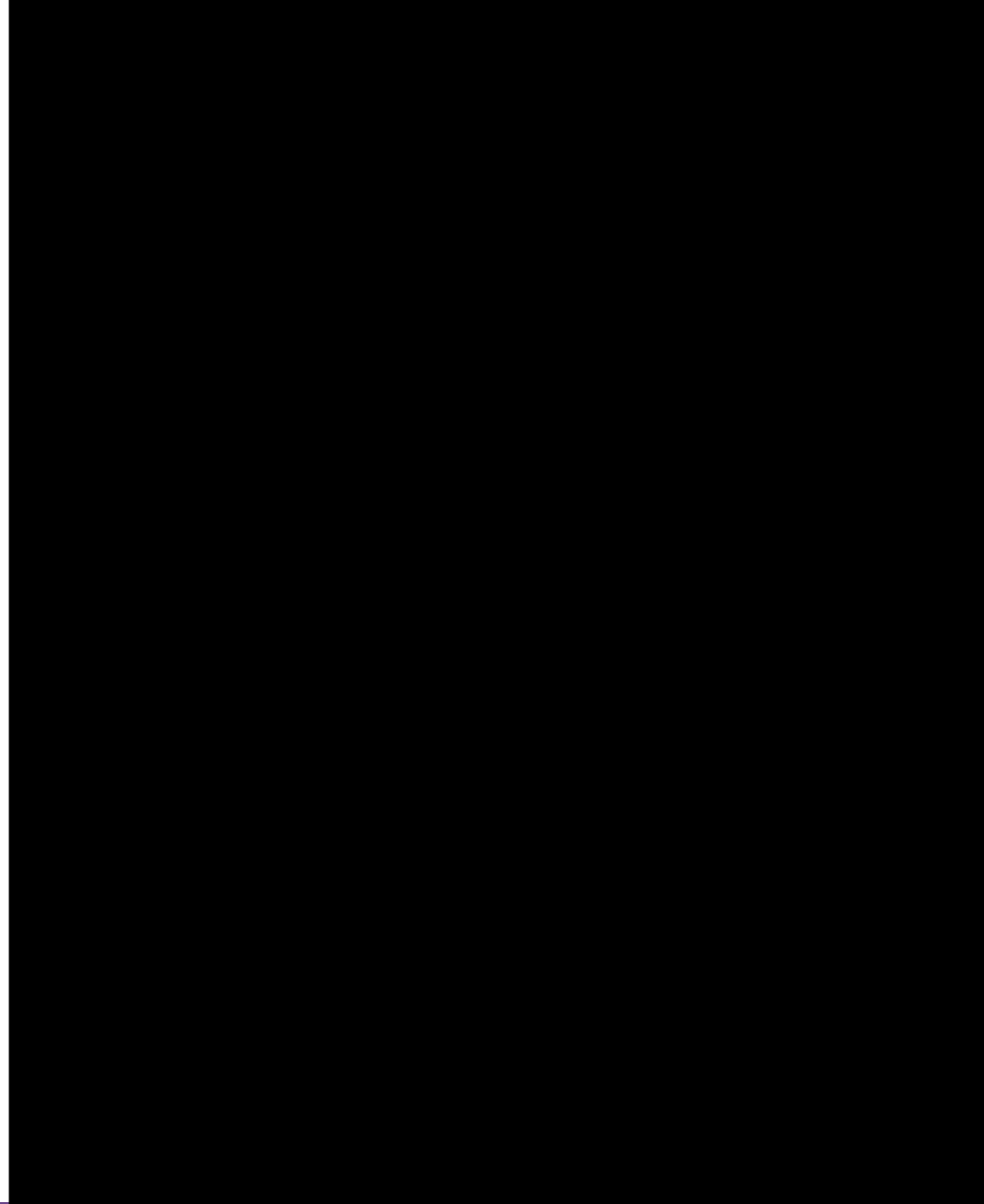
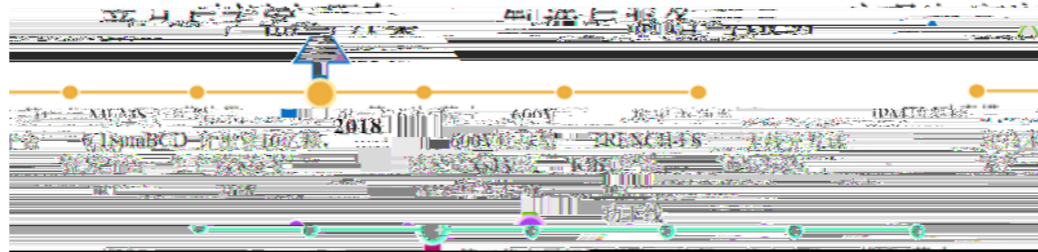
2018



wind



2008年-2018年公司关键产品与工艺发展情况



1

IDM

MOSFET

IGBT SBD FRD

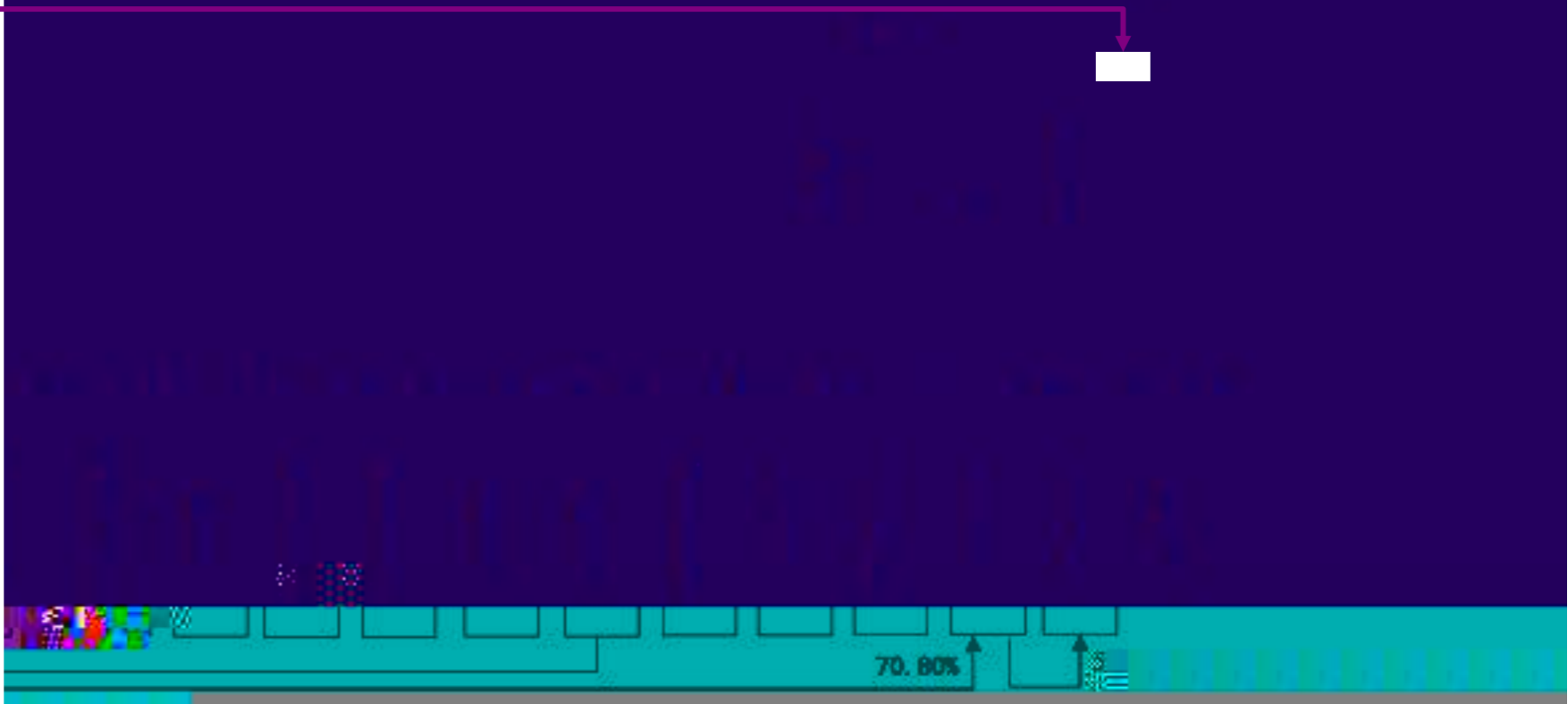
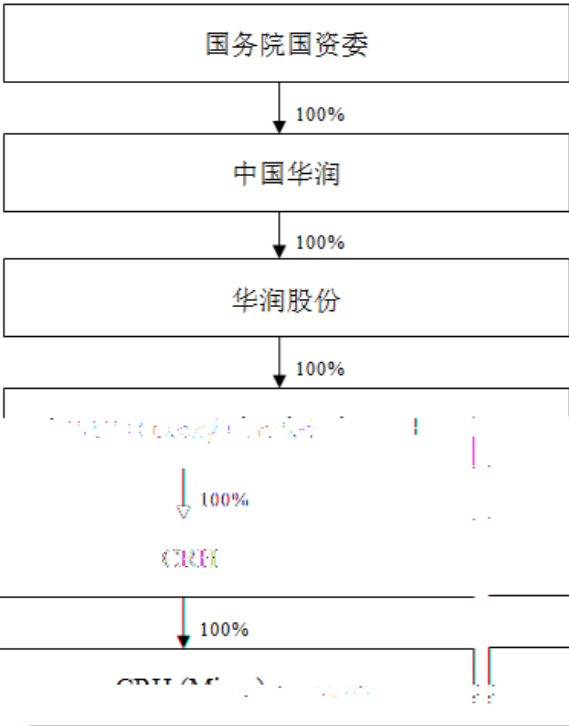


1 8 3 6 1.0-0.11 μ m
IEMS SOI BCD CMOS CMOS Bipolar BiCMOS
GaN SiC



100%

202001



2

2019Q1-3	41.32	2.70
2019Q1-3	22.38%	8.58%
	4.50	36.93%



2019Q1-3

41.32

2.70

2017

2018

14.73%

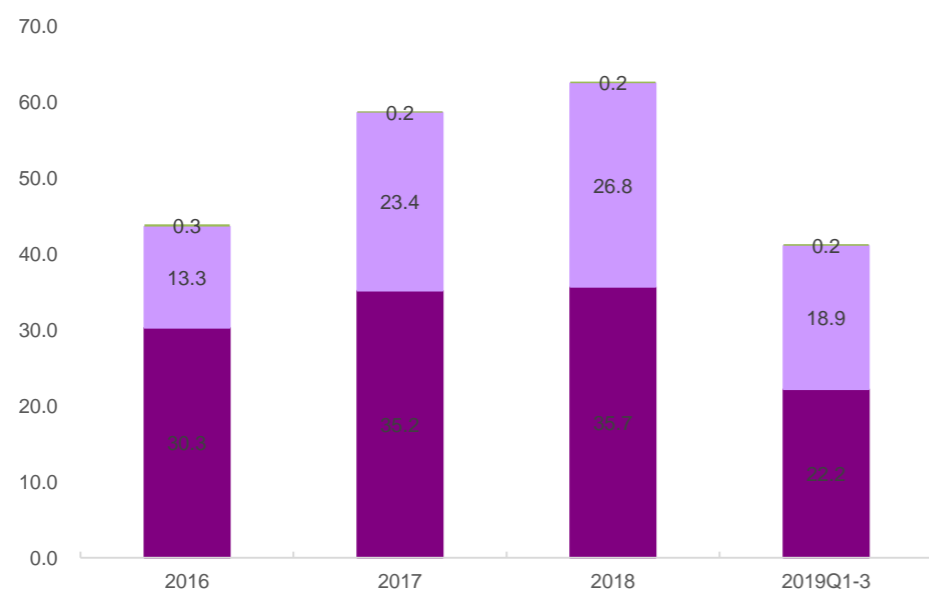
1.48%

2019H1

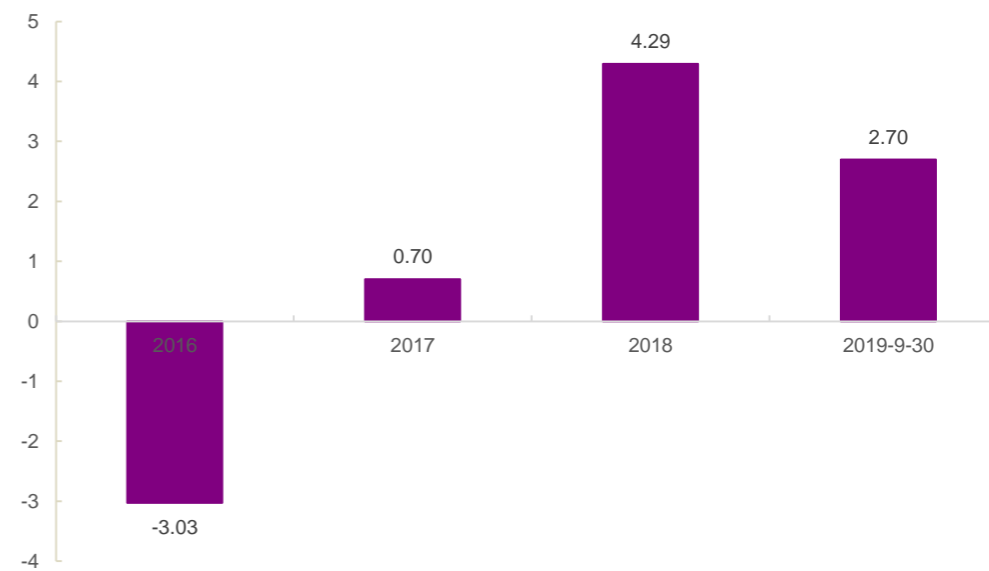
2019Q1-3

41.32

2.70



wind



wind



2019Q1-3

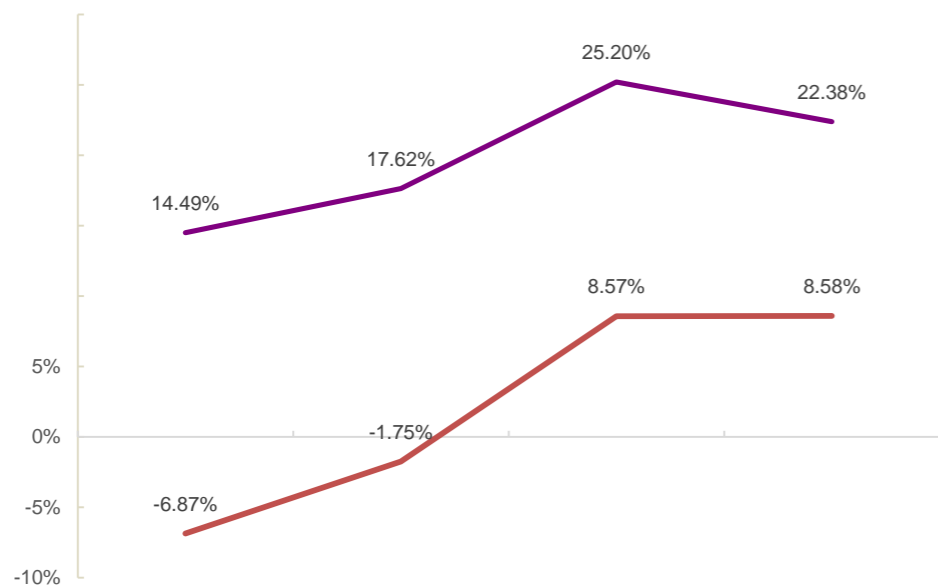
22.38%

8.58%

2018
2018

2017
2017

3.49



wind

wind







4.50

36.93%

2018

4.50

7.17%

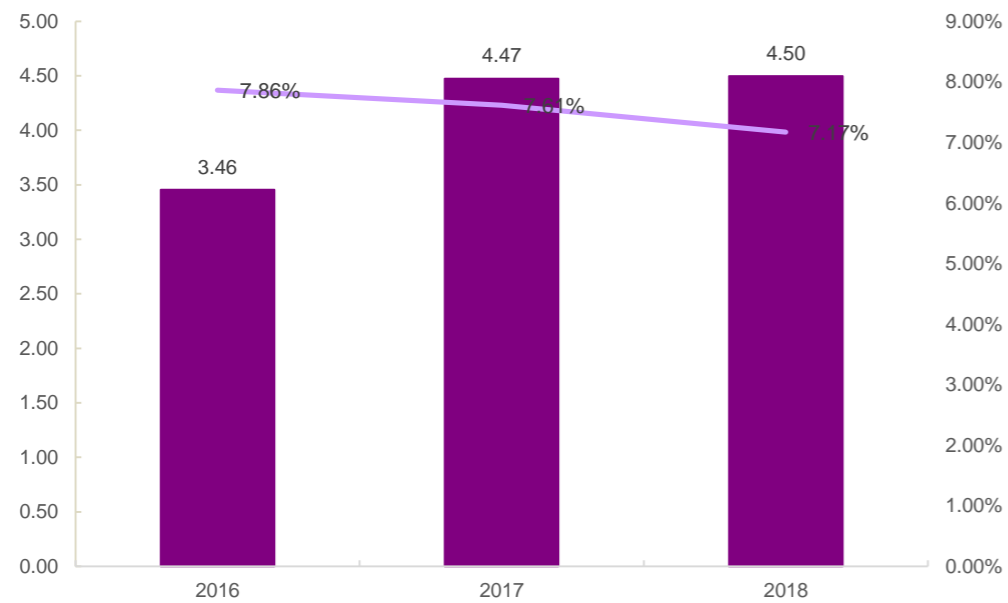
2019 6 30

7,937

641

2,290

36.93%



wind





2018

80%

80%



3

MOEFET

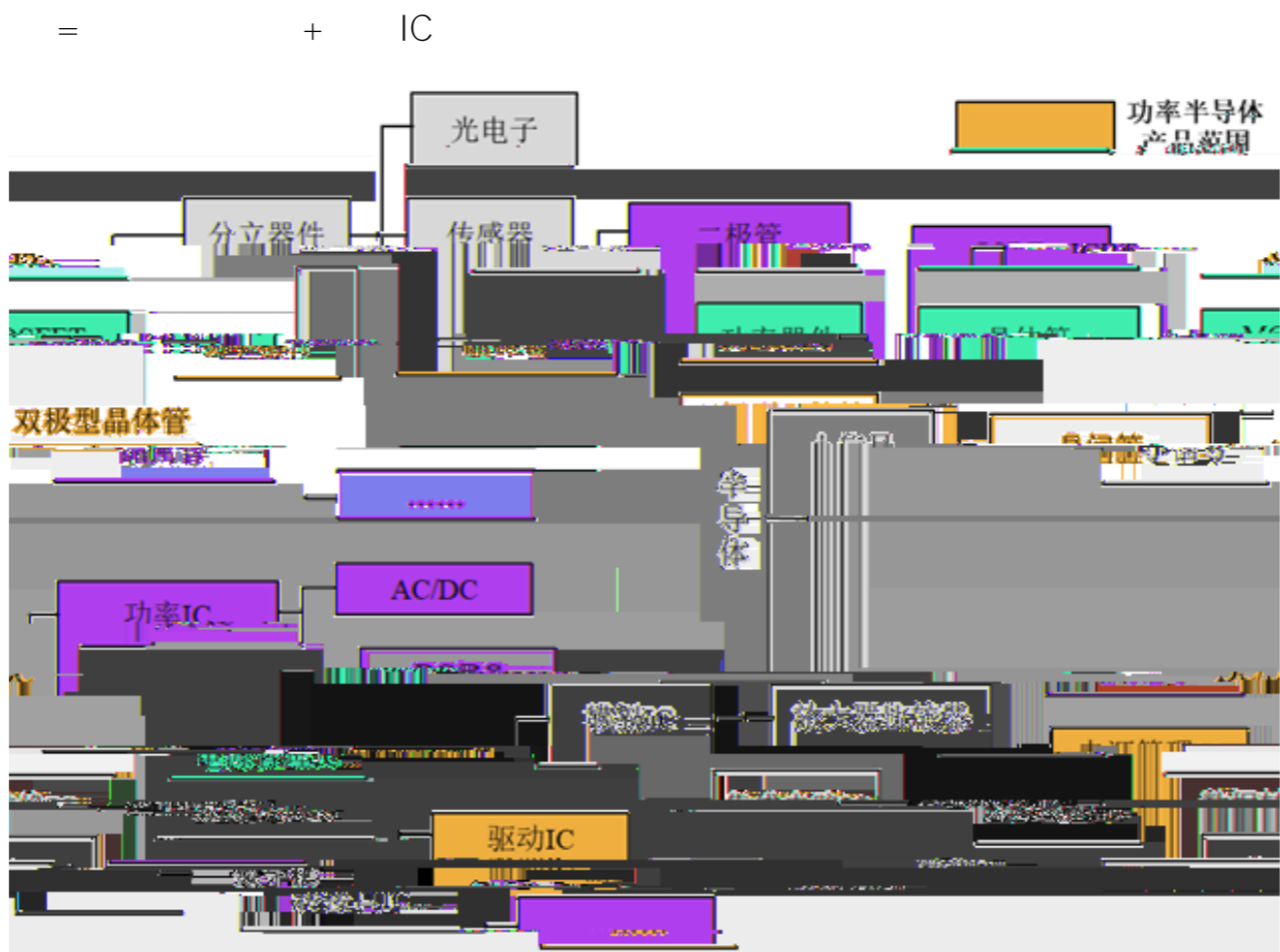
$$\begin{array}{rcccl} & & = & + & \text{IC} \\ 2020 & 422 & & 153 & 4\% \\ & & & \text{MOEFET} & \\ & \text{IDM} & & & \end{array}$$





= + IC

IC
IHS Markit MOSFET IGBT 5



2020

422

153

4%

IHS Markit

2018

391

2021

441

4.1%







IDM

2018

10

10

IDM

2018



1

2

3

4

5

8

8

8

BCD

BCD

MEMS

8

MEMS

16,000

IC

MEMS

50% 20% 30%

1	8	15	50%
2		6	20%
3		3	10%
4		6	20%
		30	100%



1

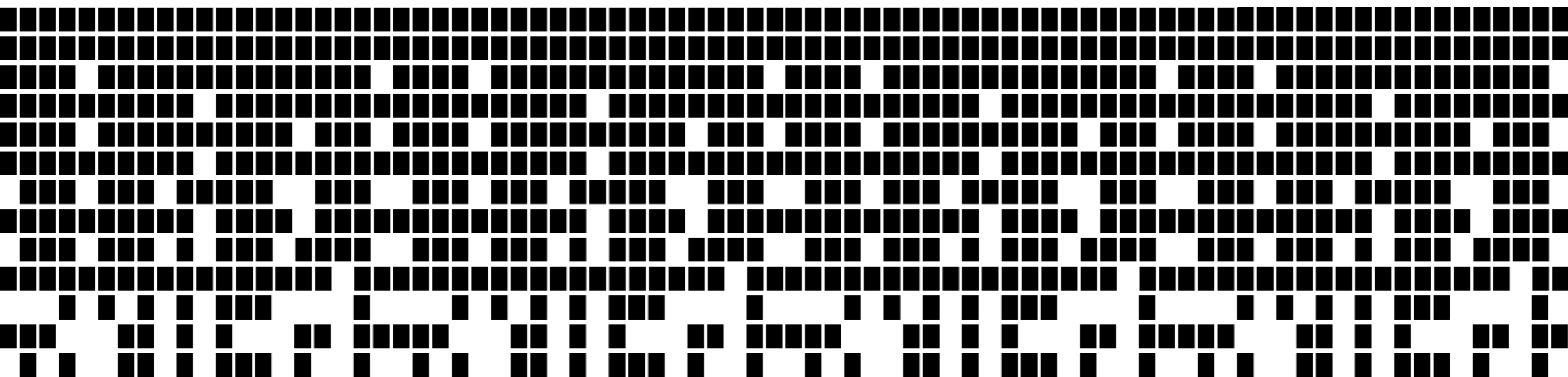
2

3

4

5





THANKYOU!



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021-52523862

wangjingwei@ebcn.com
0755-34945524

—	6-12		15%		
—	6-12		5%	15%	
—	6-12				-5% 5%
—	6-12		5%	15%	
—	6-12		15%		

A 300

" " 1996

" "

